

600 V tandem extra fast diode

Datasheet - production data

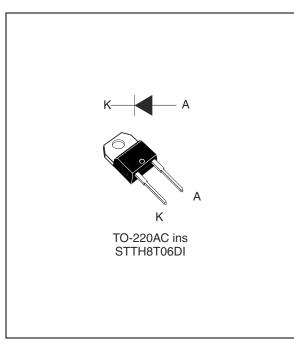


Table 1. Device summary

Symbol	Value
I _{F(AV)}	8 A
V _{RRM}	600 V
t _{rr} (typ)	15 ns
I _{RM} (typ)	2.3 A
V _F (typ)	2.05 V
I _{FRM)}	40 A
T _j (max)	175 °C

Features

- · High voltage rectifier
- Tandem diodes in series
- Very low switching losses
- Insulated device with internal ceramic
- Equal thermal conditions for both 300 V diodes
- Static and dynamic equilibrium of internal diodes are warranted by design
- Insulated package:
 - Capacitance: 7 pF
 - Insulated voltage: 2500 V rms

Description

This device is part of ST's second generation of 600 V tandem diodes. It has ultralow switching-losses with a minimized Q_{RR} (6 nC) that makes it perfect for use in circuits working in hard-switching mode. In particular the V_F/Q_{RR} trade-off positions this device between standard ultrafast diodes and silicon-carbide Schottky rectifiers in terms of price/performance ratio.

The device offers a new positioning giving more flexibility to power-circuit designers looking for good performance while still respecting cost constraints.

Featuring ST's Turbo 2 600 V technology, the device is particularly suited as a boost diode in continuous conduction mode power factor correction circuits.

Characteristics STTH8T06

1 Characteristics

Table 2. Absolute ratings (limiting values at T_j = 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V	Panatitiva paak rayarsa valtaga	T _j from 25 to 150 °C	600	V
V RRM	V _{RRM} Repetitive peak reverse voltage	T _j = -40 °C	550	V
I _{F(RMS)}	Forward rms current	14	Α	
I _{F(AV)}	Average forward current, δ = 0.5 T_c = 100 °C		8	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			Α
I _{FRM}	Repetitive peak forward current	40	Α	
T _{stg}	Storage temperature range	-65 to +175	°C	
Tj	Operating junction temperature	-40 to +175	°C	

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	2.8	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	$V_R = V_{RRM}$			10	
IR A Reverse leakage current	T _j = 125 °C	VR - VRRM		30	300	μA	
V _F ⁽²⁾ Forward voltage drop		T _j = 25 °C	I _F = 8 A		2.95		V
VF` ′	i orward voltage drop	T _j = 150 °C	IF = 0 A		2.05	2.55	V

- 1. Pulse test: $t_p = 5$ ms, $\delta < 2\%$
- 2. Pulse test: t_p = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 1.75 \text{ x } I_{F(AV)} + 0.10 I_{F}^{2}_{(RMS)}$$

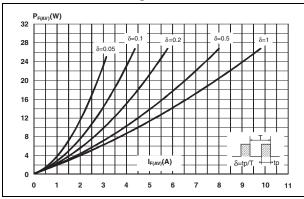
STTH8T06 Characteristics

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions			Тур.	Max.	Unit
	t _{rr} Reverse recovery time	T 25.00	$I_F = 1 \text{ A}, V_R = 30 \text{ V},$ $dI_F/dt = -50 \text{ A}/\mu\text{s}$		23	30	
t _{rr}		T _j = 25 °C	I _F = 8 A, V _R = 400 V, dI _F /dt = -200 A/μs		15	20	ns
		T _j = 125 °C	I _F = 8 A, V _R = 400 V, dI _F /dt = -200 A/μs		22		
	I _{RM} Reverse recovery current S Softness factor	T _j = 25 °C			0.8	1.1	Α
'RM		T _j = 125 °C			2.3	3	
S		T _j = 25 °C	$I_F = 8 \text{ A}, V_R = 400 \text{ V},$		1.6		
3 Solitiess factor	T _j = 125 °C	dI _F /dt = -200 A/µs		0.8		-	
	Daversa vasavani ahavas	T _j = 25 °C			6		nC
Q _{RR}	Reverse recovery charge	T _j = 125 °C			28		IIC

Figure 1. Average forward power dissipation versus average forward current

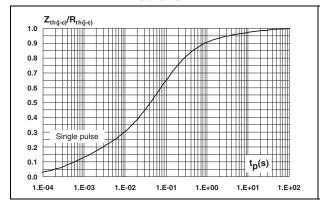
Figure 2. Forward voltage drop versus forward current (typical values)

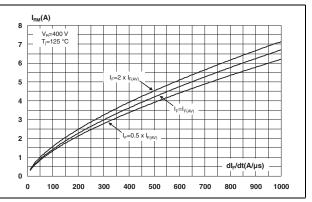


10.0 1_{FM}(A)
10.0 1_{T,=150 °C}
1.0 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 5.5 6.0 6.5 7.0

Figure 3. Relative variation of thermal impedance, junction to case, versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)





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Figure 5. Reverse recovery time versus dl_F/dt (typical values)

t_{RR}(ns) 50 V_R=400 V T_j=125 °C 40 30 20 10 dl_F/dt(A/μs) 0 0 600 700 800 100 200 300 400 500

Figure 6. Reverse recovery charges versus dl_F/dt (typical values)

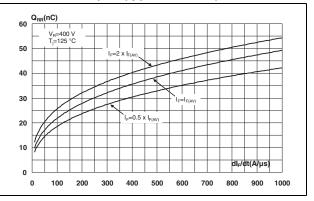


Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values)

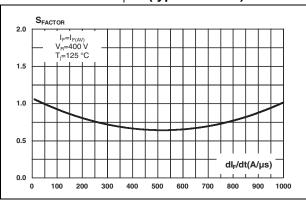


Figure 8. Relative variations of dynamic parameters versus junction temperature

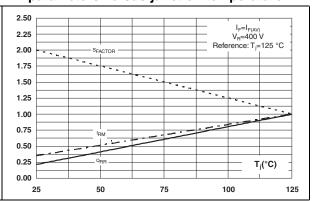
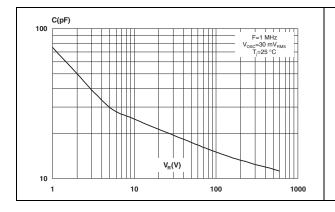
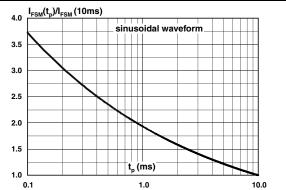


Figure 9. Junction capacitance versus reverse voltage applied (typical values)

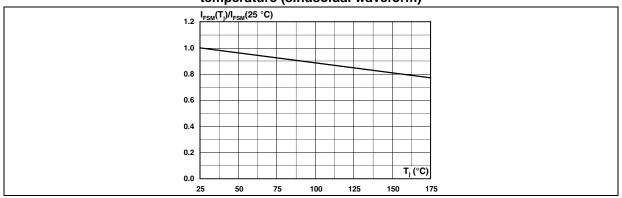
Figure 10. Relative variation of non-repetitive peak surge forward current versus pulse duration





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Figure 11. Relative variation of non-repetitive peak surge forward current versus initial junction temperature (sinusoidal waveform)



Package information STTH8T06

2 Package information

• Epoxy meets UL94, V0

• Cooling method: by conduction (C)

Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 12. T0-220AC ins dimension definitions

STTH8T06 Package information

Table 6. T0-220AC ins dimension values

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	15.20		15.90	0.598		0.625	
a1		3.75			0.147		
a2	13.00		14.00	0.511		0.551	
В	10.00		10.40	0.393		0.409	
b1	0.61		0.88	0.024		0.034	
b2	1.23		1.32	0.048		0.051	
С	4.40		4.60	0.173		0.181	
c1	0.49		0.70	0.019		0.027	
c2	2.40		2.72	0.094		0.107	
е	4.80		5.40	0.189		0.212	
F	6.20		6.60	0.244		0.259	
ØI	3.75		3.85	0.147		0.151	
14	15.80	16.40	16.80	0.622	0.646	0.661	
L	2.65		2.95	0.104		0.116	
I2	1.14		1.70	0.044		0.066	
М		2.60			0.102		

Ordering information STTH8T06

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH8T06DI	STTH8T06DI	TO-220AC ins	2.30 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
16-Oct-2012	1	Initial release
07-Nov-2012	2	Expanded description section
11-Apr-2013	3	Added Figure 10 and Figure 11.

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